

L Number	Hits	Search Text	DB	Time stamp
79	189	(gan or ingan or ga near n) and (selective near2 growth or lateral\$2 near2 overgrow\$4) and (led or laser or light near2 emitting) and (mirror or reflector or reflecting)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/16 10:40
80	11	(gan or ingan or ga near n) and (selective near2 growth or lateral\$2 near2 overgrow\$4) and (led or light near2 emitting) and (mirror or reflector or reflecting or reflect or tir) not laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/16 09:56
81	32	(image adj display) same (plural or plurality) near3 laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/16 10:40
82	52	(image near2 display) same (plural or plurality) near3 laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/16 10:42
83	6	(image near2 display) same (plural or plurality) near3 led and (ingan or gan or ga near n)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/16 10:46
84	523	(mocvd or cvd) near10 (gan or ingan or nitride or ga near n) same (degrees or misorient\$3 or offset)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/16 10:49
85	41	(mocvd) near10 (gan or ingan or nitride or ga near n) same (degrees or misorient\$3 or offset)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/16 10:52
86	3	(mocvd) same (gan or ingan or nitride or ga near n) same substrate near2 (degrees or misorient\$3 or offset)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/16 10:53
87	19	(mocvd) same (gan or ingan or nitride or ga near n) same substrate near5 (degrees or misorient\$3 or offset or miscut or deg or angled or angle)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/16 11:32
88	10	(hexagonal or wurtzite) and ("c+" near3 (facet or face or orientation or slant or plane))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/16 11:35
89	20	("c+" near3 (facet or face or orientation or slant or plane))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/16 11:35
90	8	(US-6072197-\$ or US-6320209-\$ or US-5727008-\$ or US-5828088-\$ or US-5732098-\$ or US-6613461-\$ or US-6252255-\$).did. or (JP-2003101156-\$).did.	USPAT; JPO	2004/01/16 11:48
-	23432	(laser or led or light adj emitting) and (crystal or crystallization or active) near5 (c-plane or c or s-plane or s or slant or slanted)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/15 13:23
-	420	(laser or led or light adj emitting) and (crystal or crystallization or active) near5 (c or s or slant or slanted) near3 (plane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/15 09:43

-	97	(laser or led or light adj emitting) and (crystal or crystallization or active) near5 (c or s or slant or slanted) near3 (plane) same (ingan or gan or nitride or ga near n)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/15 10:04
-	9	(laser or led or light adj emitting) and (crystal or crystallization or active or selective or buffer) near5 (pyramid or pyramidal or hexangular) near3 (plane) same (ingan or gan or nitride or ga near n)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/15 10:07
-	378	(laser or led or light adj emitting) and (crystal or crystallization or active or selective or buffer or growth or layer) near8 (slant or slanted or angle or angled or s or c) near3 (plane or planar or orientation or oriented) same (ingan or gan or nitride or ga near n)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/15 12:58
-	2	5727008.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/15 12:12
-	9	("4912063"   "5008735"   "5027168"   "5187547"   "5200022"   "5387804"   "5393993"   "5432808"   "5585648").PN.	USPAT	2004/01/15 12:10
-	10	5727008.URPN.	USPAT	2004/01/15 12:11
-	2	6072197.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/15 12:14
-	2	("5604763"   "5625202").PN.	USPAT	2004/01/15 12:12
-	10	6072197.URPN.	USPAT	2004/01/15 12:12
-	2	6320209.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/15 16:02
-	2	("5880485"   "6051849").PN.	USPAT	2004/01/15 12:16
-	3	6320209.URPN.	USPAT	2004/01/15 12:16
-	86	(laser or led or light adj emitting) and (crystal or crystallization or active or selective or buffer or growth or layer or ingan or gan or nitride or ga near n) near10 (s near plane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/15 13:00
-	43	(laser or led or light adj emitting) and (crystal or crystallization or active or selective or buffer or growth or layer) near8 (s near plane) and (ga near n or nitride or ingan or gan)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/15 13:00
-	8	nitride and "c+" near plane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/15 13:52
-	8	"c+" near plane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/15 13:52
-	10	"c+" near2 plane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/15 13:54
-	105	nitride and "c+"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/15 13:58

-	16	"c+" near2 (face or plane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/15 13:59
-	2	5981977.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/15 16:02
-	64	(gan or ingan or ga near n) and (hexagonal) near3 (prismoid or prismoidal or pyramid or pyramidal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/15 16:54
-	478	(gan or ingan or ga near n) and (selective near2 growth)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/15 16:54
-	269	(gan or ingan or ga near n) and (selective near2 growth) and (led or laser or light near2 emitting) and (electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/15 16:55
-	393	(gan or ingan or ga near n) and (selective near2 growth) and (led or laser or light near2 emitting)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/16 09:45